

Product Specification

XBLW SSM3J332R

P-Channel Enhancement Mode MOSFET

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Description

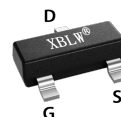
The SSM3J332R uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

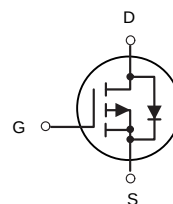
- $V_{DS} = -30V$ $I_D = -4.2A$
- $R_{DS(ON)} < 54m\Omega @ V_{GS}=10V$
- $R_{DS(ON)} < 77m\Omega @ V_{GS}=4.5V$

Application

- Battery protection
- Load switch
- Uninterruptible power supply



SOT-23-3L



P-Channel MOSFET

Package Marking and Ordering Information

Product Model	Package Type	Marking	Packing	Packing Qty
XBLW SSM3J332R	SOT-23-3L	X1KX	Tape	3000Pcs/Reel

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	± 12	V
I_D	Drain Current-Continuous	-4.2	A
I_{DM}	Drain Current-Pulsed (Note 1)	-30	A
P_D	Maximum Power Dissipation	1.2	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	°C
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 2)	104	°C/W

Electrical Characteristics (TA=25°C unless otherwise noted)

Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-24V, V _{GS} =0V	-	-	-1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±10V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-0.7	-1	-1.3	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-4.2A	-	46	54	mΩ
		V _{GS} =-4.5V, I _D =-4A	-	58	77	mΩ
		V _{GS} =-2.5V, I _D =-1A		74	130	mΩ
Forward Transconductance	g _{FS}	V _{DS} =-5V, I _D =-4.2A	-	10	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{Iss}	V _{DS} =-15V, V _{GS} =0V, F=1.0MHz	-	880	-	PF
Output Capacitance	C _{Oss}		-	105	-	PF
Reverse Transfer Capacitance	C _{rss}		-	65	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =-15V, I _D =-4.2A V _{GS} =-10V, R _{GEN} =6Ω	-	7	-	nS
Turn-on Rise Time	t _r		-	3	-	nS
Turn-Off Delay Time	t _{d(off)}		-	30	-	nS
Turn-Off Fall Time	t _f		-	12	-	nS
Total Gate Charge	Q _g	V _{DS} =-15V, I _D =-4.2A, V _{GS} =-4.5V	-	8.5	-	nC
Gate-Source Charge	Q _{gs}		-	1.8	-	nC
Gate-Drain Charge	Q _{gd}		-	2.7	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =-4.2A	-	-	-1.2	V

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

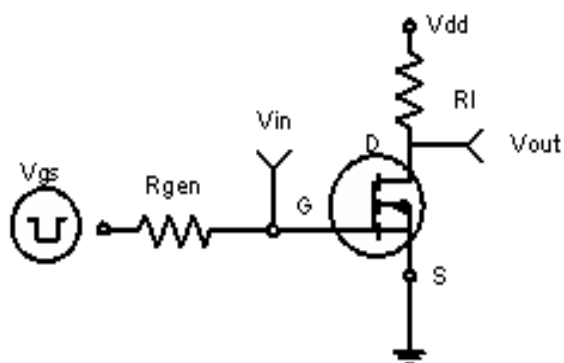


Figure 1: Switching Test Circuit

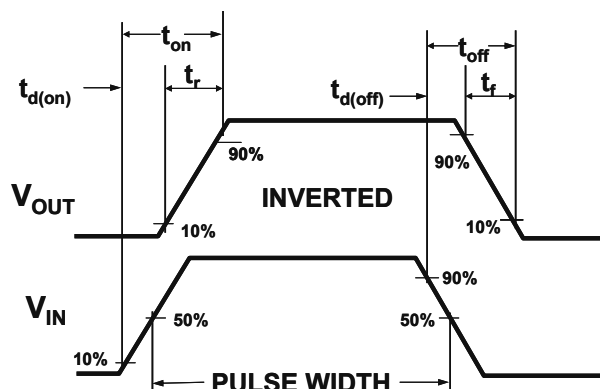
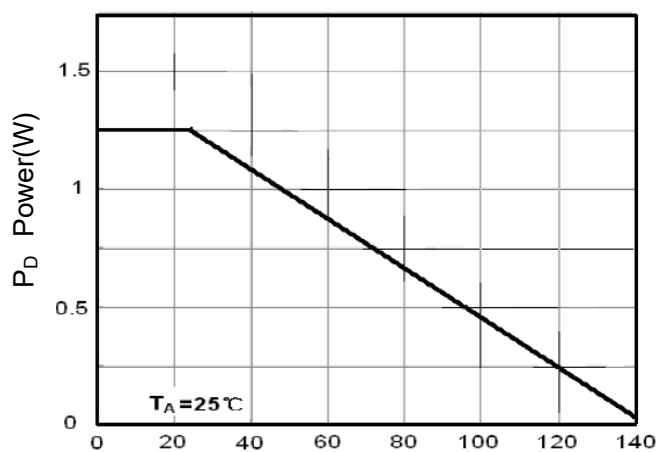
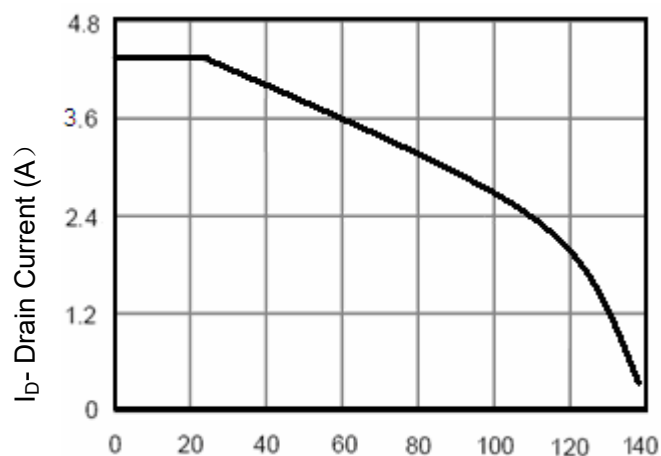


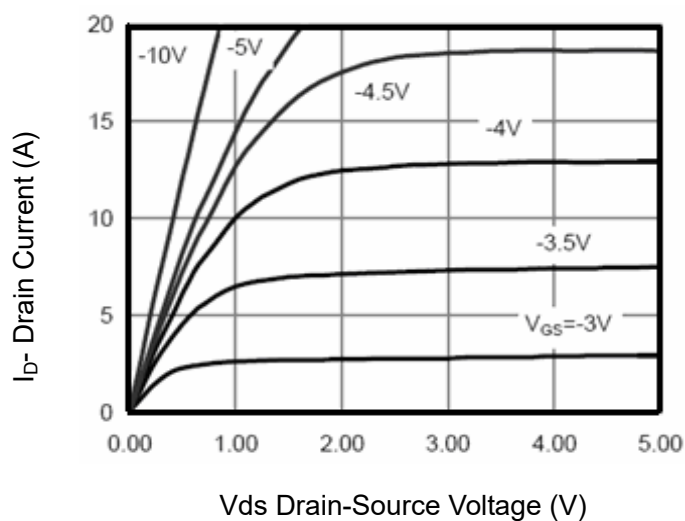
Figure 2: Switching Waveforms



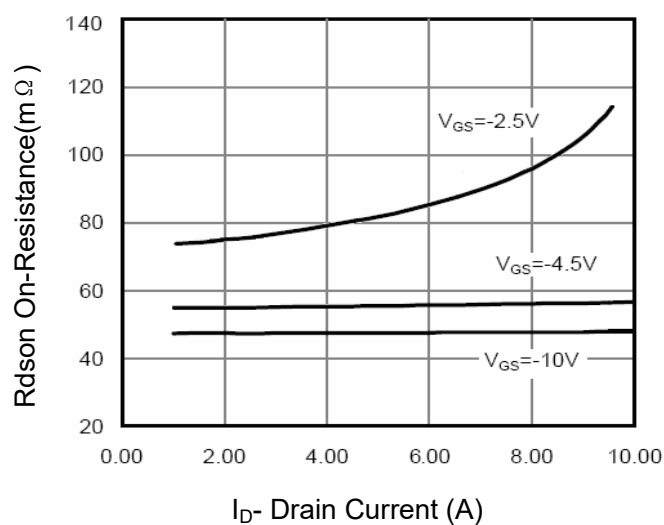
T_J-Junction Temperature(°C)
Figure 3 Power Dissipation



T_J-Junction Temperature(°C)
Figure 4 Drain Current



V_{ds} Drain-Source Voltage (V)
Figure 5 Output Characteristics



ID-Drain Current (A)
Figure 6 Drain-Source On-Resistance

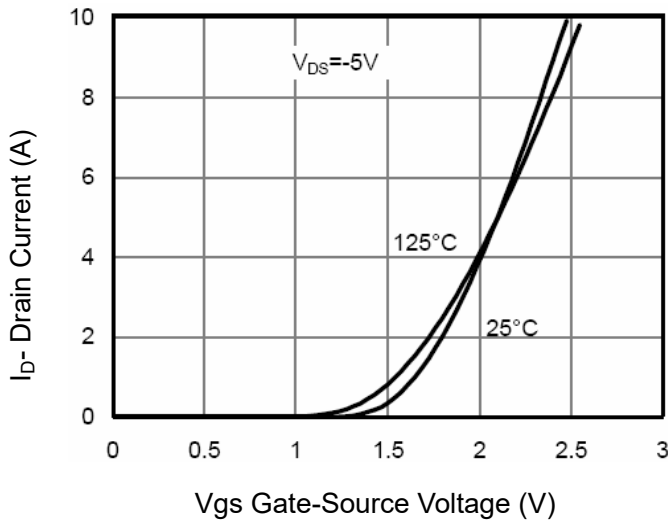


Figure 7 Transfer Characteristics

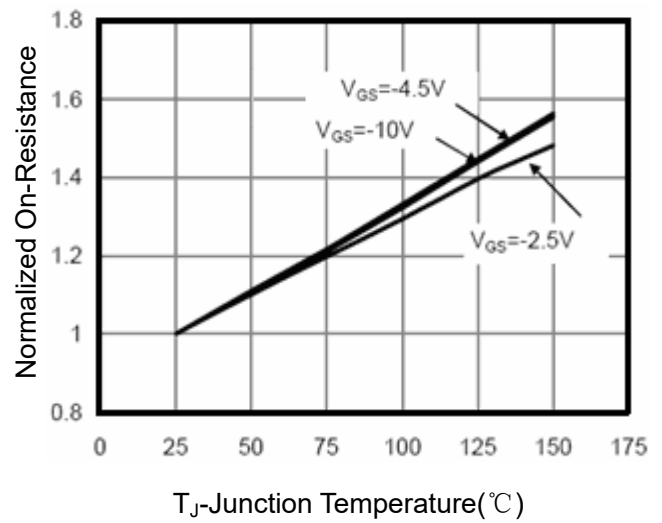


Figure 8 Drain-Source On-Resistance

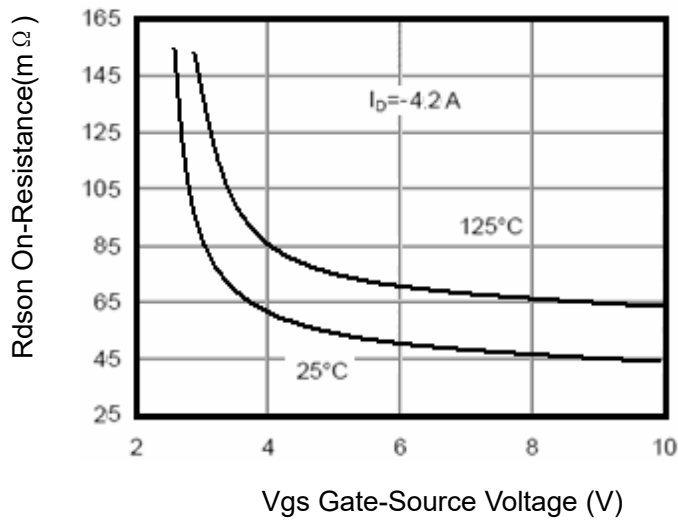


Figure 9 Rdson vs Vgs

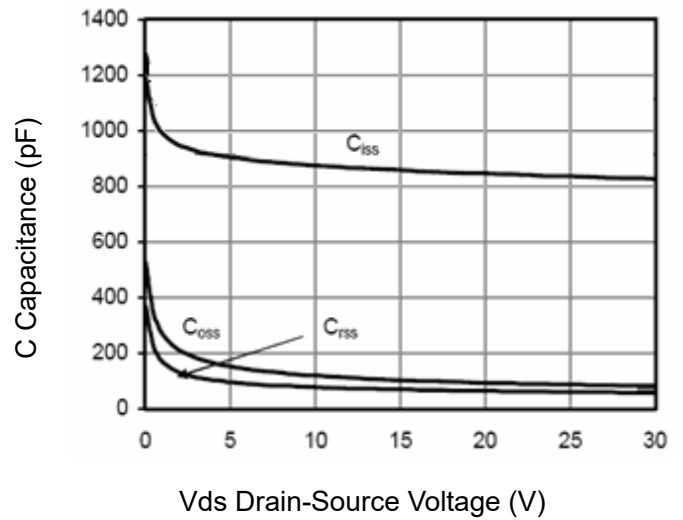


Figure 10 Capacitance vs Vds

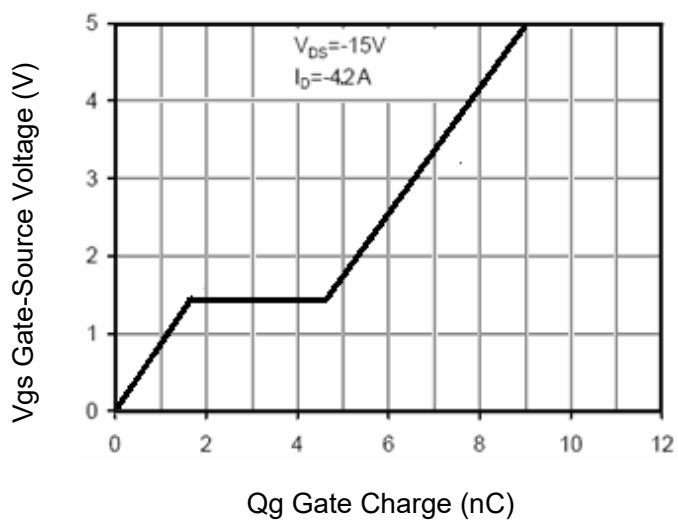


Figure 11 Gate Charge

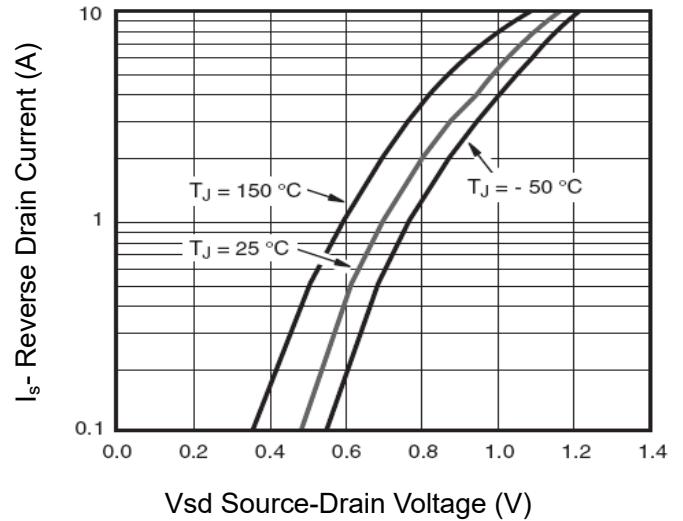
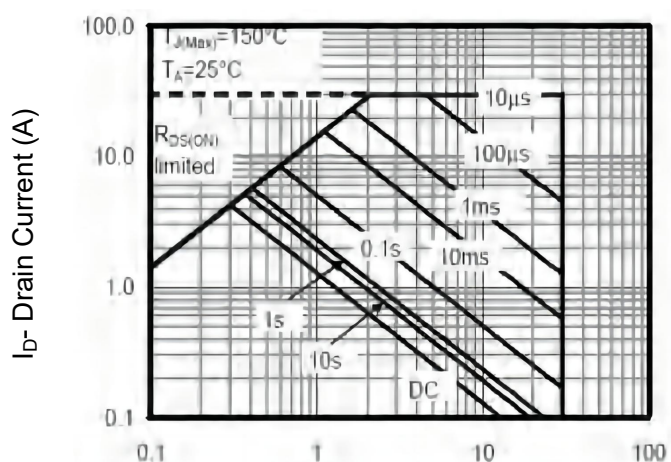
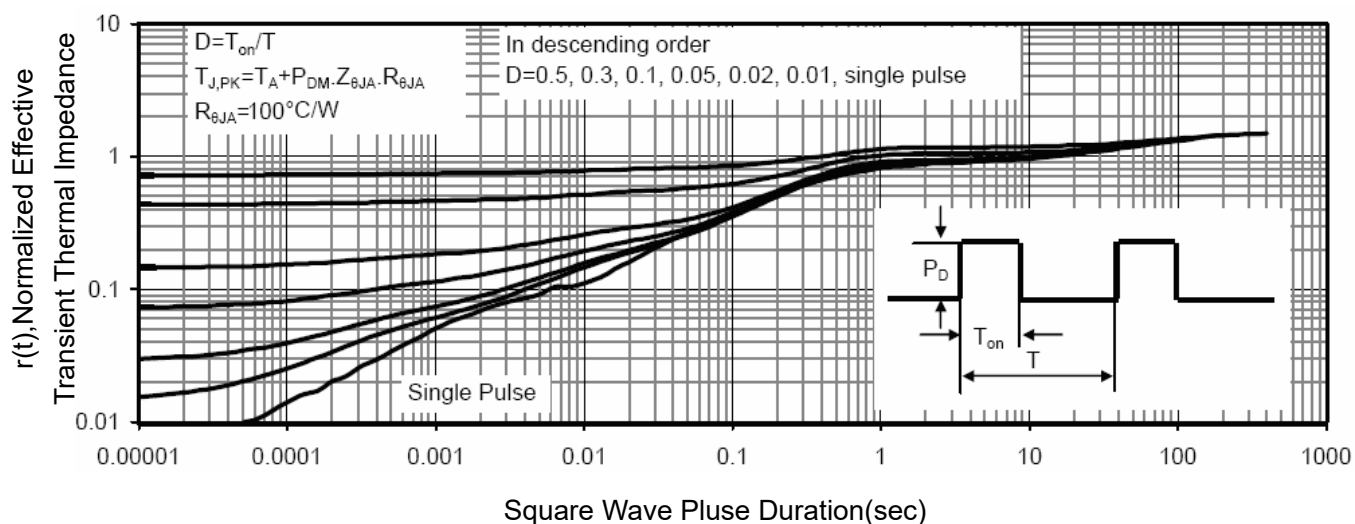


Figure 12 Source- Drain Diode Forward



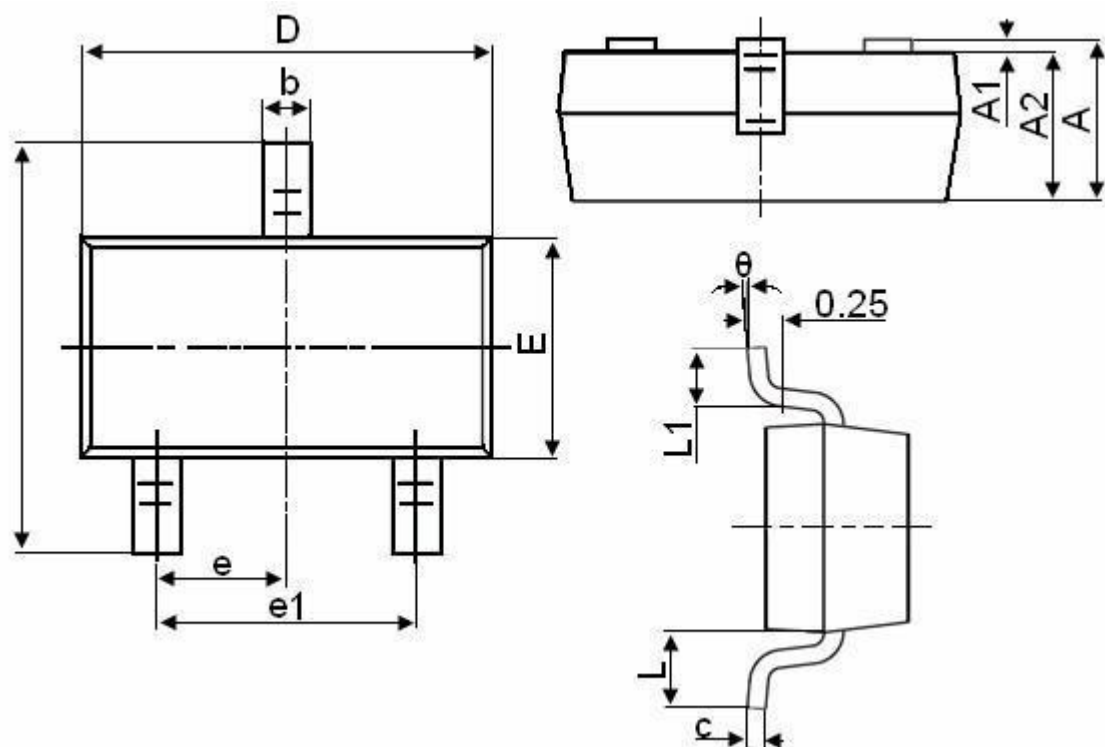
Vds Drain-Source Voltage (V)
Figure 13 Safe Operation Area



Square Wave Pluse Duration(sec)
Figure 14 Normalized Maximum Transient Thermal Impedance

Package Information

SOT23-3L



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	1.050	1.250
A1	0.000	0.100
A2	1.050	1.150
b	0.300	0.500
c	0.100	0.200
D	2.800	3.000
E	1.500	1.700
E1	2.650	2.950
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.600
θ	0°	8°

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